

## IN THE CLAIMS

The following listing of claims replaces all previous listings and versions of claim in this application.

1. (Currently Amended) A method of fabricating a ~~carrier~~ substrate comprising:

providing a crystalline ~~or mono-crystalline~~ base substrate that includes a front face and a zone of weakness which cooperatively define for defining a carrier sublayer therebetween, wherein the zone of weakness defines a remainder of the base substrate on an opposite side of the zone of weakness from the carrier sublayer;

growing a stiffening layer on the front face of the base substrate ~~to a thickness of approximately 1  $\mu$ m to approximately 10  $\mu$ m~~ to form a carrier substrate for subsequent processing;

detaching the stiffening layer and carrier sublayer from the remainder of the base substrate at the zone of weakness to obtain the a carrier substrate that is ~~and a remainder of the base substrate, the carrier substrate being~~ suitable for use in growing high quality homo-epitaxial or hetero-epitaxial films thereon; and

growing a high quality homo-epitaxial film or hetero-epitaxial film on the stiffening layer ~~to form~~ of the carrier substrate .

2. (Cancelled).

3. (Currently Amended) The method of claim 2 which further comprises implanting atomic species ~~hydrogen ions~~ into the ~~front face of the~~ base substrate to a controlled mean implantation depth to form the zone of weakness within the base substrate that defines the sub-layer.

4. (Cancelled)

5. (Cancelled).

6. (Original) The method of claim 1 wherein the sub-layer is less than approximately 5 $\mu$ m thick.

7. (Original) The method of claim 1 which further comprises conducting a thermal treatment to detach the carrier substrate from the base substrate.

8. (Original) The method of claim 3 which further comprises providing a sacrificial layer on the front face of the base substrate prior to implanting atomic species.

9. (Currently Amended) The method of claim 8 wherein the sacrificial layer is a ~~thin~~ silicon dioxide (SiO<sub>2</sub>) layer.

10. (Original) The method of claim 8 which further comprises removing the sacrificial layer before providing the stiffening layer.

11. (Original) The method of claim 1 which further comprises growing the stiffening layer by at least one of epitaxial growth, molecular beam epitaxy (MBE), metal-organic chemical vapor deposition (MOCVD), hydride vapor phase epitaxy (HVPE) or by sputtering.

12. (Currently Amended) The method of claim 1 wherein the stiffening layer has a thickness ~~is in the range~~ of approximately 5  $\mu$ m to at least approximately 10 $\mu$ m ~~thick~~.

13. (Currently Amended) The method of claim 1 which further comprises pre-treating the front face ~~surface~~ of the base substrate prior to growing the stiffening layer by using at least one of HF etching, plasma etching, or a standard cleaning treatment.

14. (Original) The method of claim 1 which further comprises providing at least one additional layer on top of the stiffening layer or between the base substrate and the stiffening layer.

15. (Currently Amended) The method of claim 14 wherein the additional layer between the base substrate and a the stiffening layer is a buffer layer, the buffer layer being made of at least one of AlN, GaN, AlGaN and ~~or~~ a combination thereof.

16. (Original) The method of claim 3 further comprising providing at least two additional layers on top of the base substrate, and wherein at least one of the additional layers is provided prior to implanting atomic species.

17. (Original) The method of claim 16 which further comprises implanting the atomic species into the at least one additional layer to create a weakened zone inside the at least one additional layer.

18. (Original) The method of claim 1 which further comprises polishing a surface of the remainder of the base substrate after detaching the carrier substrate such that the base substrate is suitable for reuse.

19. (Original) The method of claim 1 wherein the base substrate is made of at least one of silicon, silicon carbide, sapphire, gallium arsenide, indium phosphide (InP) or germanium (Ge).

20. (Currently Amended) The method of claim 1 ~~wherein a homo-epitaxial film is grown on the stiffening layer and~~ wherein the stiffening layer is epitaxially grown and is made of the same material as a the homo-epitaxial film that is to be grown on the carrier substrate in a subsequent fabricating step.

21. (Currently Amended) The method of claim 1 wherein the stiffening layer has a crystalline structure and a thermal expansion coefficient similar to that of ~~an~~ the epitaxial film to be grown on the carrier substrate in a subsequent fabricating step.

22. (Original) The method of claim 1 wherein the stiffening layer is made out of at least one of gallium nitride (GaN), aluminum nitride (AlN), indium nitride (InN), silicon germanium (SiGe), indium phosphite (InP), gallium arsenide (GaAs) or alloys made out of those materials.

23. (Original) The method of claim 22 wherein the alloys include at least one of AlGaN, InGaN, InGaAs or AlGaAs.

24. (Currently Amended) The method of claim 1 wherein a ~~backside~~ surface of the carrier substrate ~~created after the detaching step~~ has a surface roughness in a range of approximately 20 Å RMS to about 200 Å RMS.

25. (Cancelled)

26. (Previously Presented) The method of claim 1, wherein a hetero-epitaxial film made out of at least one of GaN, SiGe, AlN, or InN is grown on the stiffening layer.

27. (Previously Presented) The method of claim 1 wherein all recited steps are conducted in the same apparatus.

28. (Previously Presented) The method of claim 1 wherein the detaching provides a surface roughness that is sufficient to securely hold the carrier substrate in position on the remainder of the base substrate due to frictional interaction.

29. (New) The method of claim 28, wherein the carrier substrate is retained in position against the remainder of the base substrate during the growth of the high quality epitaxial film.

30. (New) The method of claim 1, wherein the crystalline base substrate is monocrystalline.

31. (New) A method of fabricating a substrate comprising:  
providing a crystalline base substrate;  
forming a zone of weakness in the base substrate for defining a carrier sublayer  
and a remainder of the base substrate;  
growing a stiffening layer on the base substrate after forming the zone of  
weakness;  
detaching the stiffening layer and carrier sublayer from the remainder of the base  
substrate at the zone of weakness to obtain a carrier substrate; and  
growing one of a homo-epitaxial layer and a hetero-epitaxial layer on the  
stiffening layer of the carrier substrate.

32. (New) The method of claim 30, wherein the stiffening layer has a  
thickness of approximately 1  $\mu\text{m}$  to approximately 10  $\mu\text{m}$ .